MJD49T4

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- SURFACE-MOUNTING TO-252 (DPAK) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICALLY SIMILAR TO TIP49

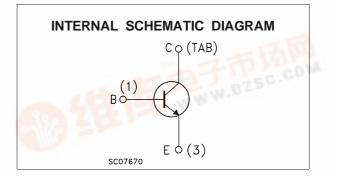
APPLICATIONS

- SWITCH MODE POWER SUPPLIES
- AUDIO AMPLIFIERS
- GENERAL PURPOSE SWITCHING AND AMPLIFIER

DESCRIPTION

The MJD49T4 is manufactured using Medium Voltage Epitaxial Planar technology, resulting in a rugged high performance cost-effective transistor.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit V	
Vсво	Collector-Base Voltage (I _E = 0)	450		
VCEO	Collector-Emitter Voltage (I _B = 0)	350	V	
V _{EBO}	Emitter-Base Voltage (I _C = 0)	5	V	
Ic	Collector Current	1	А	
I _{CM}	Collector Peak Current (t _p < 5 ms)	2	А	
IB	Base Current	0.6	А	
IBM	Base Peak Current (t _p < 5 ms)	1.2		
Ptot	Total Dissipation at $T_c = 25 \ ^{\circ}C$	15		
Tstg	Storage Temperature	-65 to 150		
Tj	Max. Operating Junction Temperature	150		



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THERMAL DATA

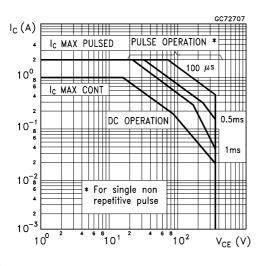
R _{thj-case}	Thermal Resistance Junction-case	Max	8.33	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

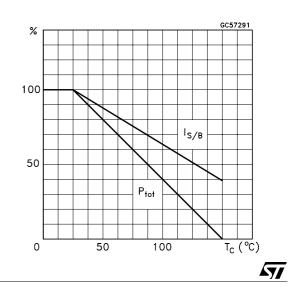
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 450 V			0.1	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 250 V			0.1	mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = 5 V$			1	mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	Ic = 30 mA	350			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1 \ {\rm A}$ $I_{\rm B} = 0.2 \ {\rm A}$			1	V
$V_{BE(on)}*$	Base-Emitter On Voltage	I _C = 1 A V _{CE} = 10 V			1.5	V
h _{FE} *	DC Current Gain		30 10		150	
f⊤	Transition Frequency	I _C = 0.2 A V _{CE} = 10 V f=2MHz	10			MHz
h _{fe}	Small Signal Current Gain	I _C = 0.2 A V _{CE} = 10 V f=1kHz	25			

* Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

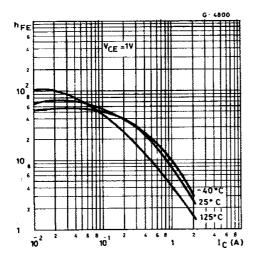
Safe Operating Area



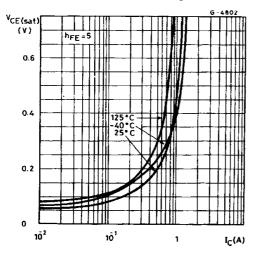
Derating Curves



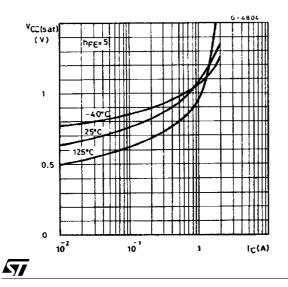
DC Current Gain



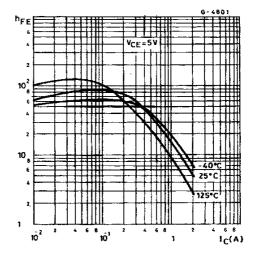
Collector-Emitter Saturation Voltage



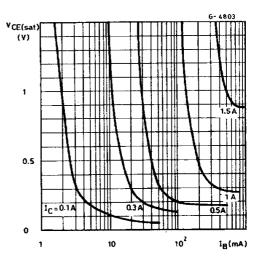
Base-Emitter Saturation Voltage



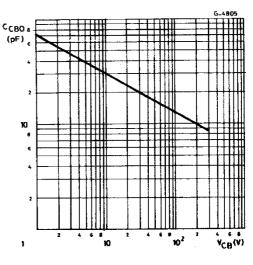
DC Current Gain

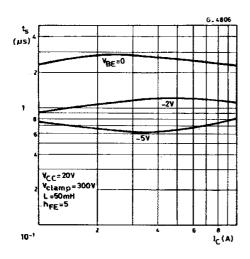


Collector-Emitter Saturation Voltage



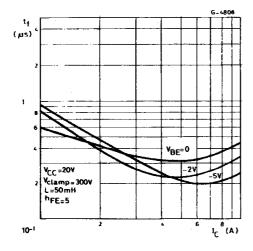
Collector-Base Capacitance



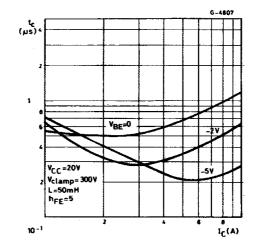


Switching Time Inductive Load

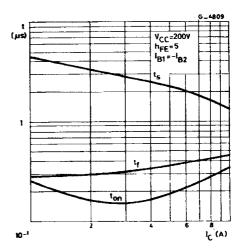
Switching Time Inductive Load



Switching Time Inductive Load



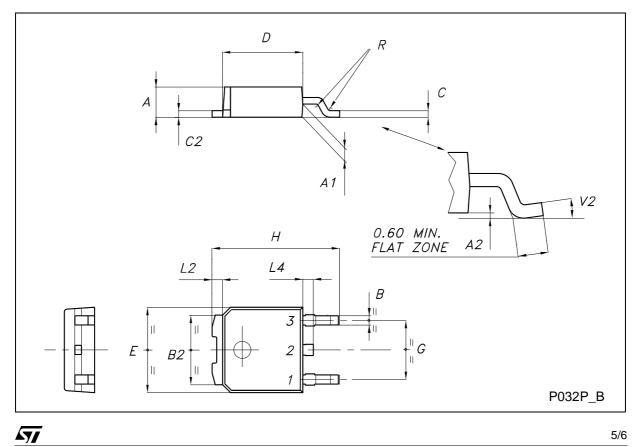




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DIM.	mm		inch			
Divi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

TO-252 (DPAK) MECHANICAL DATA



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